

METHOD FOR SEMICONDUCTOR WAFER ETCHING

Abstract of the Disclosure

A batch-type etching method includes applying microwaves from the outside of a reaction chamber to semiconductor wafers after HF gas etching of the wafers to remove residual substances including H_2O , CH_3OH , CH_3COOH and/or other by-products from surfaces of the wafers. Microwaves oscillate polar molecules of the substances and generate heat, thereby removing the substances.

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